

FDP6021P/FDB6021P

20V P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

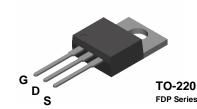
This P-Channel power MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for power management applications.

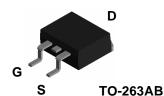
Applications

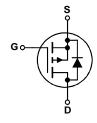
- Battery management
- Load switch
- Voltage regulator

Features

- -28 A, -20 V. $R_{DS(ON)} = 30 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 40 \text{ m}\Omega$ @ $V_{GS} = 2.5 \text{ V}$ $R_{DS(ON)} = 65 \text{ m}\Omega$ @ $V_{GS} = 1.8 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low R_{DS(ON)}
- 175°C maximum junction temperature rating







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V	
V _{GSS}	Gate-Source Voltage	± 8	V	
I _D	Drain Current - Continuous	(Note 1)	-28	Α
	- Pulsed	(Note 1)	-80	
P _D	Total Power Dissipation @ T _C = 25°C		37	W
	Derate ab	ove 25°C	0.25	W°C
T _J , T _{STG}	Operating and Storage Junction Temper	-65 to +175	°C	

FDB Series

Thermal Characteristics

R _{θJC}	Thermal Resistance, Junction-to-Case	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Package Marking and Ordering Information

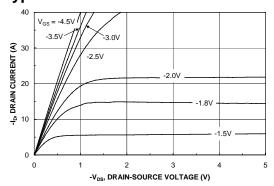
Device Marking	Device	Reel Size	Tape width	Quantity
FDP6021P	FDP6021P	Tube	n/a	45
FDB6021P	FDB6021P	13"	24mm	800 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	I		I	I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT, _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ}C$		-16		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)			•		•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.7	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ}C$		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		24 31 50 30	30 40 65 42	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-40			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -14 \text{ A}$		33		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1890		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		302		pF
C _{rss}	Reverse Transfer Capacitance			124		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$		13	23	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		10	20	ns
t _{d(off)}	Turn-Off Delay Time	7		80	128	ns
t _f	Turn-Off Fall Time	1		50	80	ns
Q _g	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -14 \text{ A},$		20	28	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		4		nC
Q_{gd}	Gate-Drain Charge	1		7		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings		•	•	
Is	Maximum Continuous Drain-Source				-28	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -14 \text{ A}$		-0.9	-1.3	V

Notes

- 1. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%
- 2. TO-220 package is supplied in tube / rail @ 45 pieces per rail.
- 3. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A

Typical Characteristics



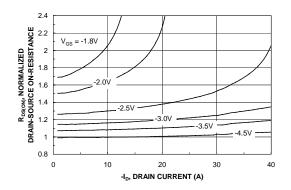
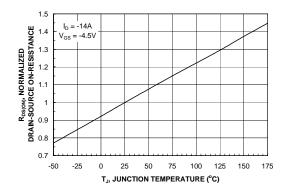


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



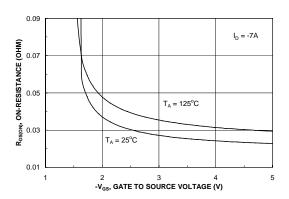
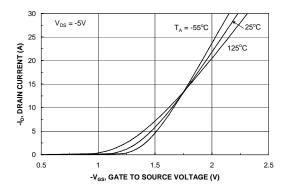


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



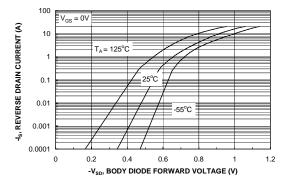


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

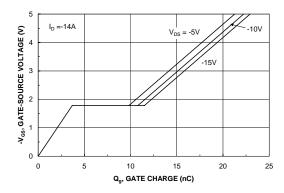
Typical Characteristics

-ID, DRAIN CURRENT (A)

10

V_{GS} = -4.5V SINGLE PULSE

 $R_{\theta JC} = 4^{\circ}C/W$ $T_A = 25^{\circ}C$



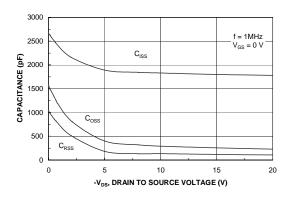


Figure 7. Gate Charge Characteristics.

10ms

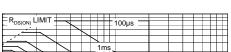




Figure 8. Capacitance Characteristics.

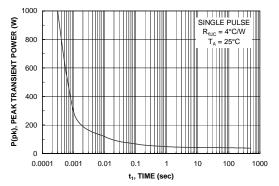


Figure 9. Maximum Safe Operating Area.

-V_{DS}, DRAIN-SOURCE VOLTAGE (V)



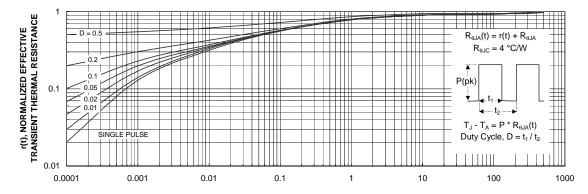
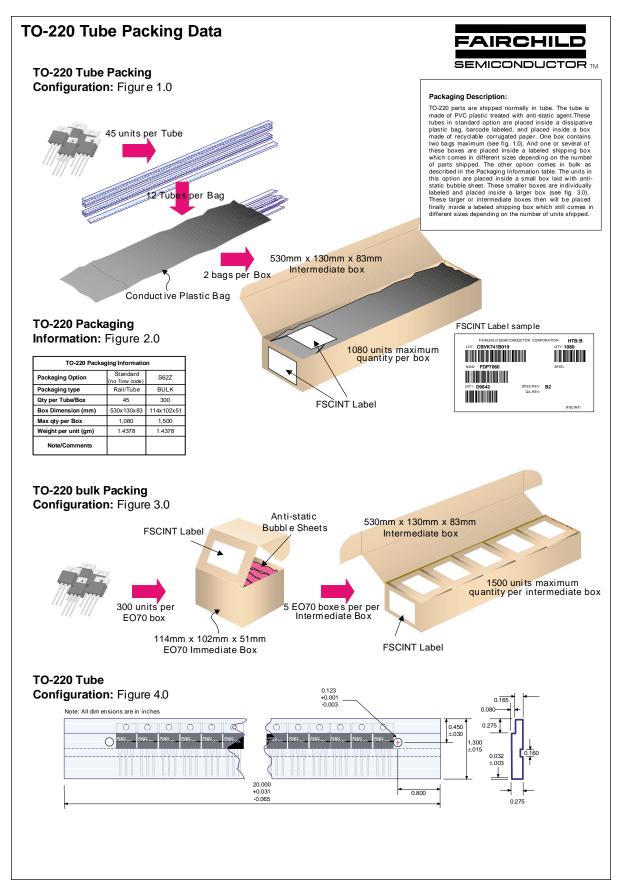


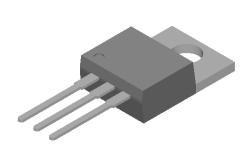
Figure 11. Transient Thermal Response Curve.

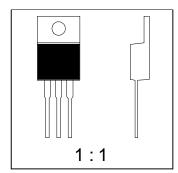


TO-220 Package Dimensions



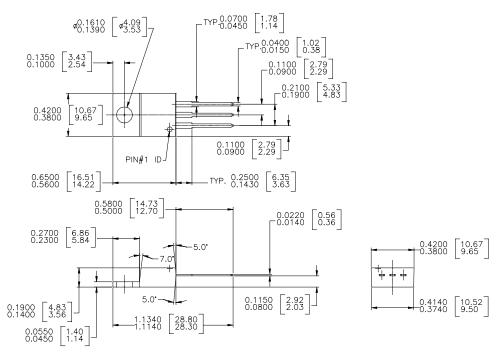
TO-220 (FS PKG Code 37)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 1.4378

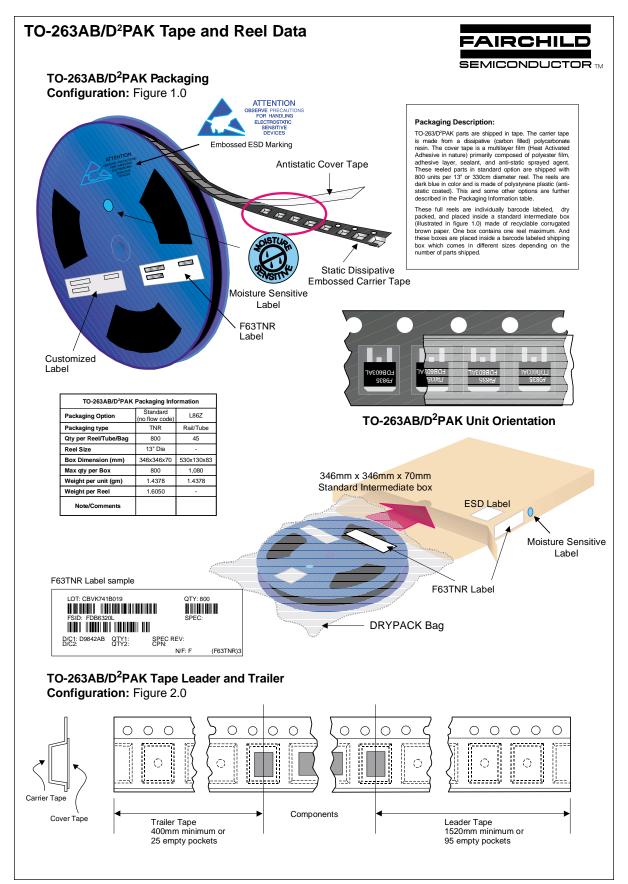


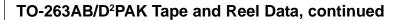
NOTE : UNLESS OTHERWISE SPECIFIED

1. STANDARD LEAD FINISH: 200 MICROINCHES / 5.08 MICRON MINIMUM LEAD / TIN 15/85 ON OLIN 194 COPPER OR EQUIVALENT

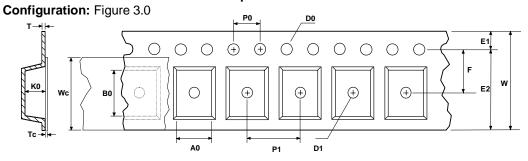
2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87

TO 220 3 LEAD





TO-263AB/D²PAK Embossed Carrier Tape



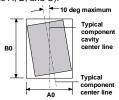
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	16.70 +/-0.20	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

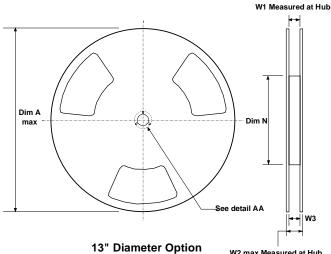


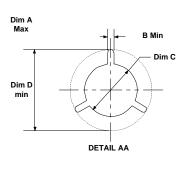
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0





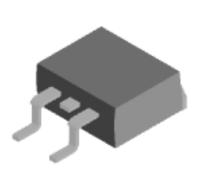
W2 max Measured at Hub

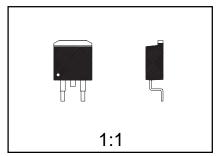
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Package Dimensions



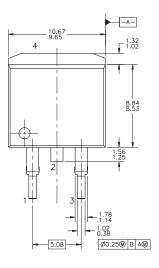
TO-263AB/D²PAK (FS PKG Code 45)

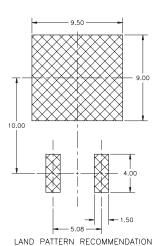


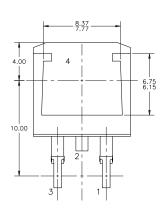


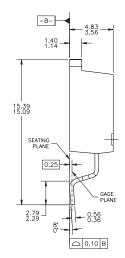
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—265, ISSUE C,
 VARIATION AB, DATED 2/92.

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Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
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